

# PJQ4425DP

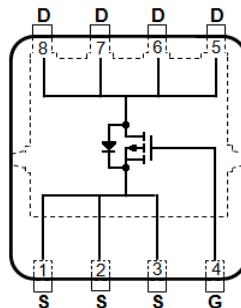
## 20V P-Channel Enhancement Mode MOSFET

**Voltage** **-20 V** **Current** **-43 A**

### Features

- $R_{DS(ON)}$ ,  $V_{GS} @ -4.5V$ ,  $I_D @ -6A < 10.5m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS} @ -2.5V$ ,  $I_D @ -4A < 15m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS} @ -1.8V$ ,  $I_D @ -2A < 24m\Omega$
- Low  $R_{DS(ON)}$
- High current rating
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

DFN3333-8L



### Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams

### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	
Continuous Drain Current( <sup>Note 4</sup> )	$I_D$	-13	A
$T_A=70^\circ C$	$I_D$	-11	
Pulsed Drain Current( <sup>Note 1</sup> )	$I_{DM}$	-85	
Power Dissipation	$P_D$	2.8	W
$T_A=70^\circ C$	$P_D$	1.8	
Continuous Drain Current( <sup>Note 4</sup> )	$I_D$	-43	A
$T_c=100^\circ C$	$I_D$	-27	
Power Dissipation	$P_D$	30	W
$T_c=100^\circ C$	$P_D$	12	
Single Pulse Avalanche Energy( <sup>Note 6</sup> )	$E_{AS}$	37	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150	°C
Typical Thermal Resistance( <sup>Note 5</sup> )	Junction to Case	$R_{\theta JC}$	4.2
	Junction to Ambient	$R_{\theta JA}$	45
			°C/W

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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-0.5	-0.77	-1.1	
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-6\text{A}$	-	8.5	10.5	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-4\text{A}$	-	11	15	
		$V_{\text{GS}}=-1.8\text{V}, I_{\text{D}}=-2\text{A}$	-	18	24	
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 10\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	$\text{nA}$
<b>Dynamic</b> <sup>(Note 7)</sup>						
Total Gate Charge	$Q_g$	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-6\text{A}, V_{\text{GS}}=-4.5\text{V}$ <sup>(Note 2,3)</sup>	-	29	-	$\text{nC}$
Gate-Source Charge	$Q_{\text{gs}}$		-	3.4	-	
Gate-Drain Charge	$Q_{\text{gd}}$		-	7.3	-	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-15\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$	-	2736	-	$\text{pF}$
Output Capacitance	$C_{\text{oss}}$		-	242	-	
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	180	-	
Gate resistance	$R_g$	$f=1.0\text{MHz}$	-	6	-	$\Omega$
Turn-On Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-10\text{V}, I_{\text{D}}=-6\text{A}, V_{\text{GS}}=-4.5\text{V}, R_{\text{G}}=25\Omega$ <sup>(Note 2,3)</sup>	-	29	-	$\text{ns}$
Turn-On Rise Time	$t_r$		-	102	-	
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	277	-	
Turn-Off Fall Time	$t_f$		-	142	-	
<b>Drain-Source Diode</b>						
Diode Forward Current	$I_s$	---	-	-	-45	A
Diode Forward Voltage	$V_{\text{SD}}$	$I_s=-1\text{A}, V_{\text{GS}}=0\text{V}$	-	-0.6	-1.0	V
Reverse Recovery Time	$T_{\text{rr}}$	$V_{\text{GS}}=0\text{V}, I_s=-6\text{A}$ $dI_s/dt=100\text{A}/\mu\text{s}$	-	12	-	ns
Reverse Recovery Charge	$Q_{\text{rr}}$		-	1.5	-	$\text{nC}$

Notes :

- 1.Pulse width<300us, Duty cycle<2%.
- 2.Essentially independent of operating temperature typical characteristics.
- 3.Repetitive rating, pulse width limited by junction temperature  $T_J(\text{MAX})=150^\circ\text{C}$ . Ratings are based on low frequency and duty cycles to keep initial  $T_J = 25^\circ\text{C}$ .
- 4.The maximum current rating is package limited.
5. $R_{\text{eJA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6.The test condition is  $L=0.1\text{mH}, I_{\text{AS}}=-27\text{A}, V_{\text{DD}}=-15\text{V}, R_{\text{G}}=25 \text{ ohm}$ , Starting  $T_J=25^\circ\text{C}$ .
- 7.Guaranteed by design, not subject to production testing.

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## TYPICAL CHARACTERISTIC CURVES

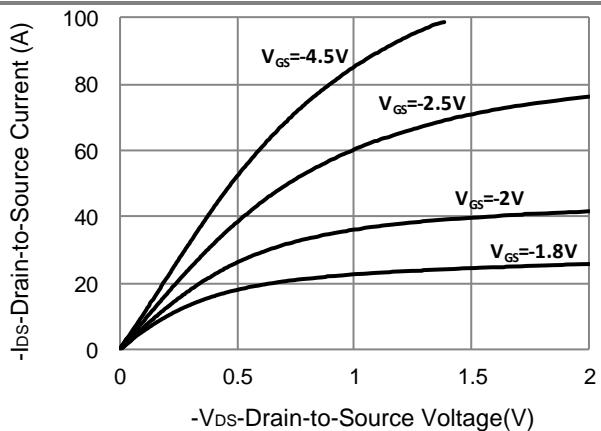


Fig.1 Output Characteristics

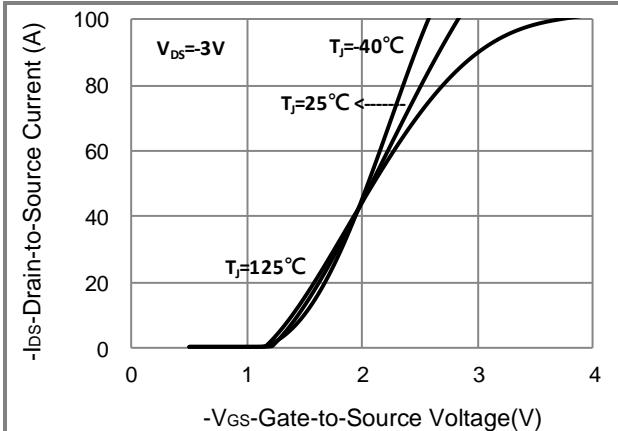


Fig.2 Transfer Characteristics

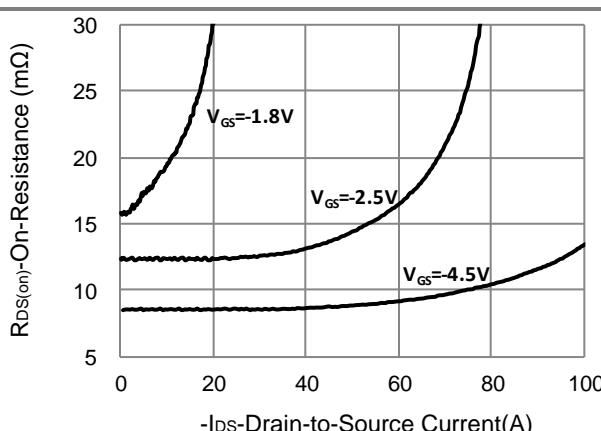


Fig.3 On-Resistance vs. Drain Current

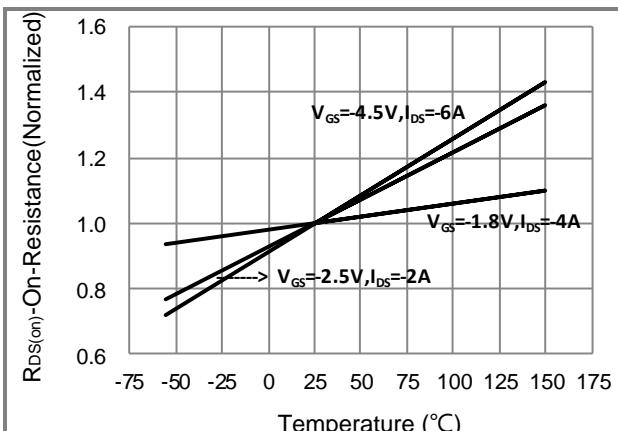


Fig.4 On-Resistance vs. Junction temperature

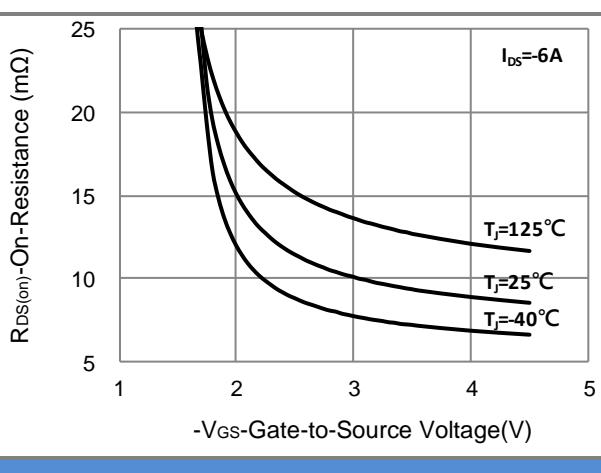


Fig.5 On-Resistance Variation with  $V_{GS}$

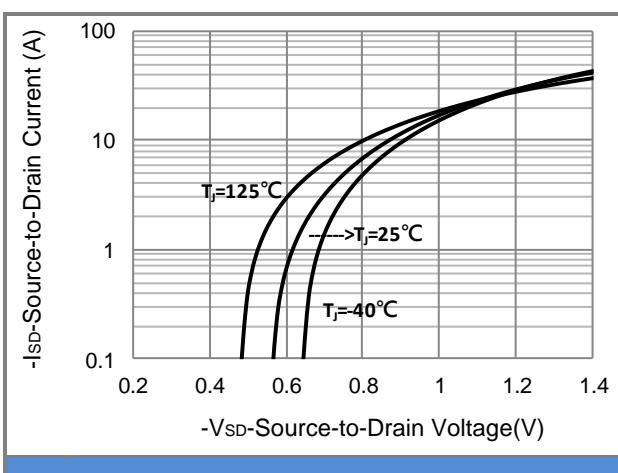


Fig.6 Source-Drain Diode Forward Voltage

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## TYPICAL CHARACTERISTIC CURVES

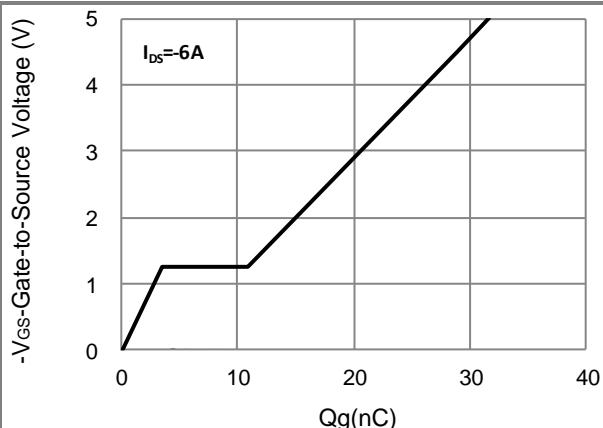


Fig.7 Gate-Charge Characteristics

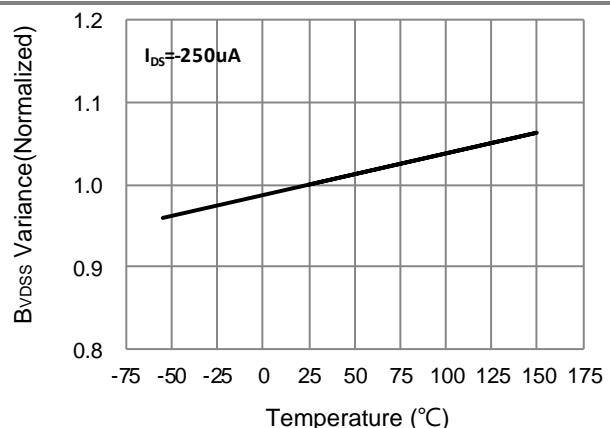


Fig.8 Breakdown Voltage Variation vs. Temperature

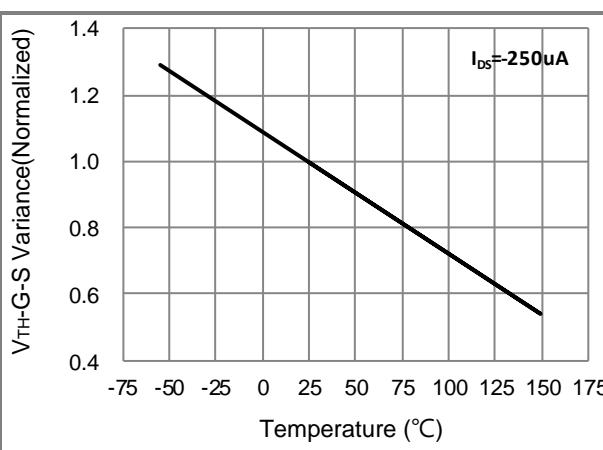


Fig.9 Threshold Voltage Variation with Temperature

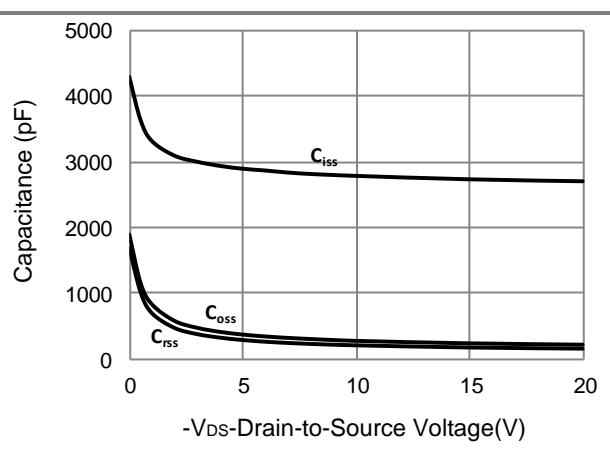


Fig.10 Capacitance vs. Drain-Source Voltage

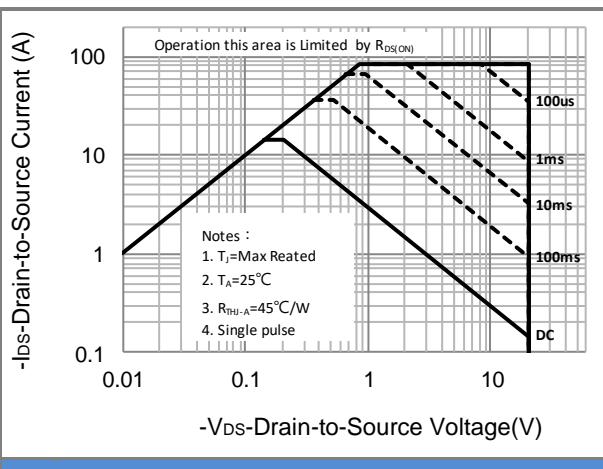


Fig.11 Maximum Safe Operating Area

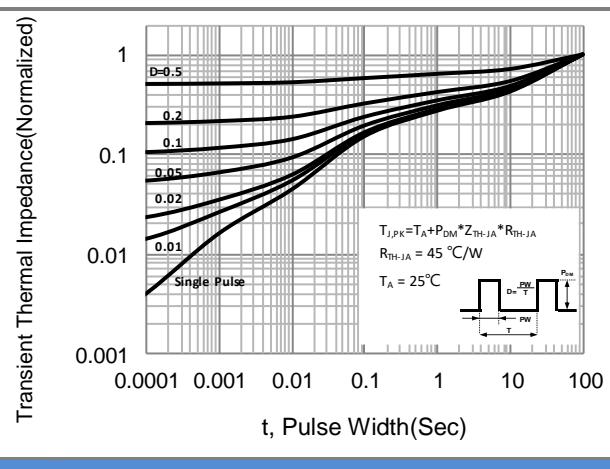


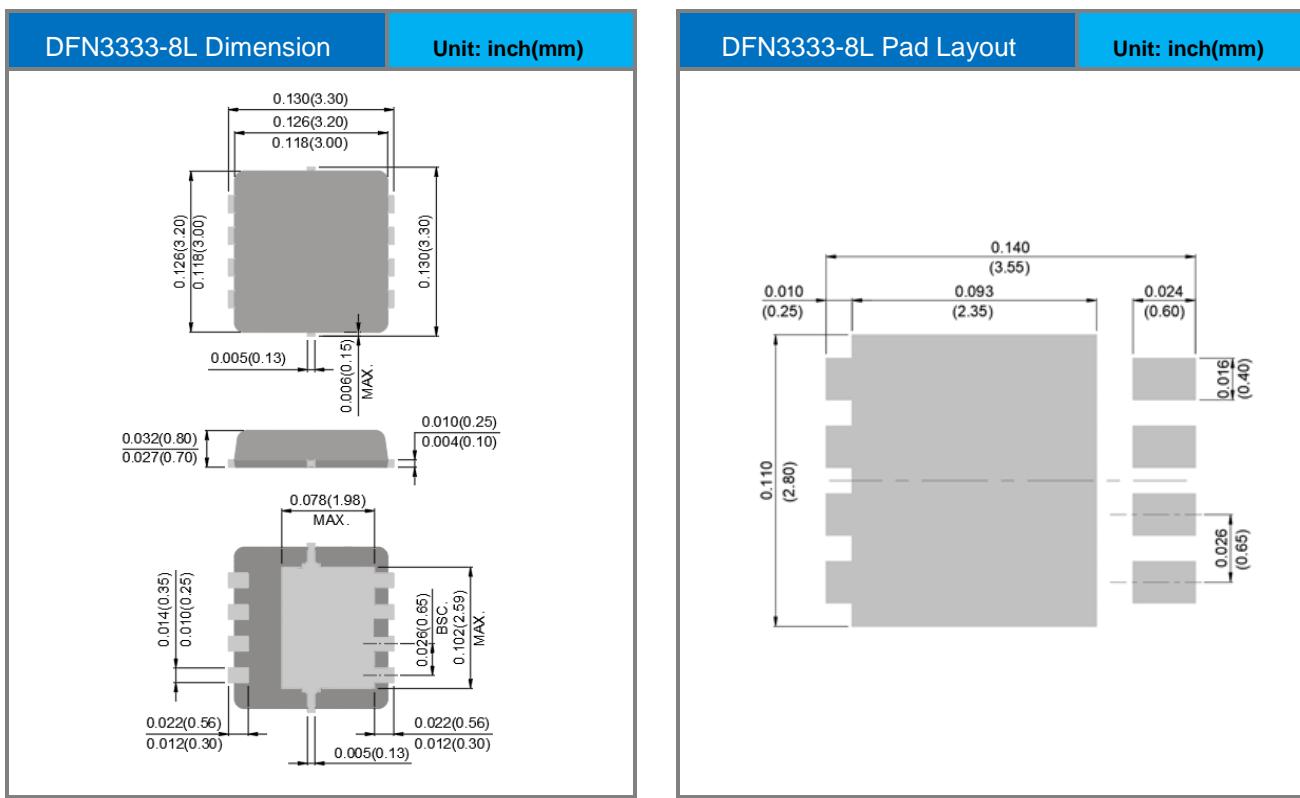
Fig.12 Normalized Transient Thermal Impedance

# PJQ4425DP

## Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4425DP_R2_00001	DFN3333-8L	5K pcs / 13" reel	4425	Halogen free RoHS compliant

## Packaging Information & Mounting Pad Layout



## PJQ4425DP

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